

## **In the Claims**

This listing of claims will replace all prior versions, and listings, of claims in the application:

## **Listing of Claims**

1. - 25. (Canceled)

26. (New): A programmable resistor device in an integrated circuit device, comprising:

a substrate with individual lines disposed between a first terminal and a second terminal, wherein any of the individual lines may be blown open by a current forced from the first terminal to the second terminal; and

a first line of the individual lines having a resistance different from a second line.

27. (New): The device according to claim 26 wherein the resistance of the first line is lower than that of the second line.

28. (New): The device according to claim 26 wherein a line width of the second line is wider than that of the first line.

29. (New): The device according to claim 26 wherein the substrate comprises a semiconductor layer.

30. (New): The device according to claim 29 wherein the semiconductor layer comprises silicon or polysilicon.

31. (New): The device according to claim 26 wherein the programmable resistor device is a chip identifier for the integrated circuit device.

32. (New): The device according to claim 26, wherein the individual lines comprise a semiconductor layer.

33. (New): A programmable resistor device in an integrated circuit device, comprising:  
a substrate with individual lines disposed between a first terminal and a second terminal, wherein any of the individual lines may be blown open by a current forced from the first terminal to the second terminal; and  
a layer of metal or metal-semiconductor alloy overlying a first line of the individual lines but not a second line of the individual lines, the first line with the layer of metal or metal-semiconductor alloy having a resistance smaller than that of the second line.

34. (New): The device according to claim 33, wherein the metal comprises metal silicide.

35. (New): The device according to claim 33 wherein the substrate comprises semiconductor layer.

36. (New): The device according to claim 33 wherein the semiconductor layer comprises silicon or polysilicon.

37. (New): The device according to claim 33, wherein the lines comprise a semiconductor layer.

38. (New): A programmable resistor device in an integrated circuit device, comprising:  
a substrate with individual lines disposed between a first terminal and a second terminal, wherein any of the individual lines may be blown open by a current forced from the first terminal to the second terminal; and  
a first line of the individual lines with a first dopant concentration and a second line of the individual lines with a second dopant concentration, the first line having a resistance smaller than that of the second line.

39. (New): The device according to claim 38 wherein the substrate comprises semiconductor layer.

40. (New): The device according to claim 38 wherein the semiconductor layer comprises silicon or polysilicon.